

iscN-Channel MOSFET Transistor

TK4R3A06PL, ITK4R3A06PL

• FEATURES

- Low drain-source on-resistance:
 $R_{DS(ON)} = 3.3m\Omega$ (typ.) ($V_{GS} = 10V$)
- Enhancement mode:
 $V_{th} = 1.5$ to $2.5V$ ($V_{DS} = 10V$, $I_D = 0.5mA$)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

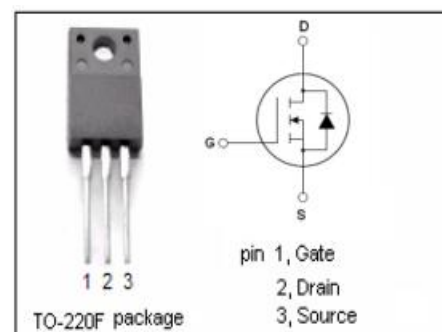
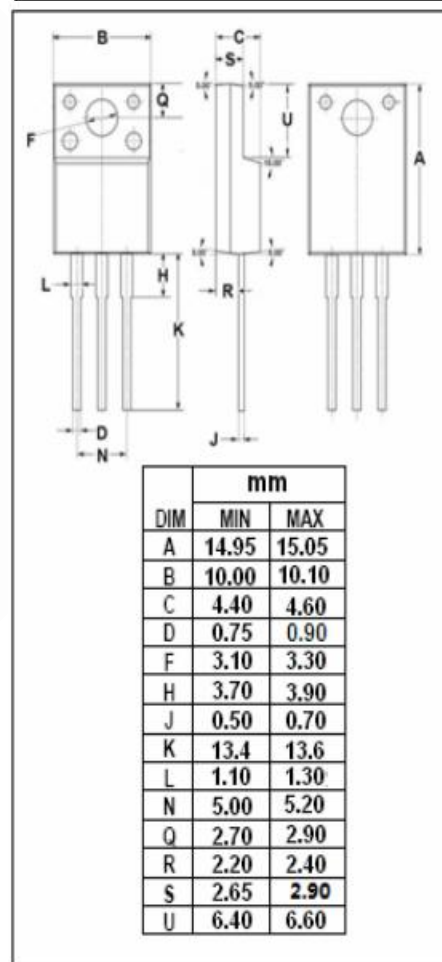
- Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	68	A
I_{DM}	Drain Current-Single Pulsed	350	A
P_D	Total Dissipation @ $T_c = 25^\circ C$	36	W
T_j	Max. Operating Junction Temperature	175	$^\circ C$
T_{stg}	Storage Temperature	-55~175	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	4.16	$^\circ C/W$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62.5	$^\circ C/W$



iscN-Channel MOSFET Transistor

TK4R3A06PL, ITK4R3A06PL

ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=10mA$	60			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=10V; I_D=0.5mA$	1.5		2.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=4.5V; I_D=15A$		5.2	7.2	$m\Omega$
		$V_{GS}=10V; I_D=34A$		3.3	4.3	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V; V_{GS}=0V$			10	μA
V_{SDF}	Diode forward voltage	$I_{DR}=68A, V_{GS}=0V$			1.5	V